NTJD1155L

Power MOSFET

8 V, ±1.3 A, High Side Load Switch with Level−Shift, P−Channel SC−88

The NTJD1155L integrates a P and N−Channel MOSFET in a single package. This device is particularly suited for portable electronic equipment where low control signals, low battery voltages and high load currents are needed. The P−Channel device is specifically designed as a load switch using ON Semiconductor state−of−the−art trench technology. The N−Channel, with an external resistor (R1), functions as a level−shift to drive the P−Channel. The N−Channel MOSFET has internal ESD protection and can be driven by logic signals as low as 1.5 V. The NTJD1155L operates on supply lines from 1.8 to 8.0 V and can drive loads up to 1.3 A with 8.0 V applied to both V_{IN} and $V_{ON/OFF}$.

Features

- Extremely Low $R_{DS(on)}$ P−Channel Load Switch MOSFET
- Level Shift MOSFET is ESD Protected
- Low Profile, Small Footprint Package
- V_{IN} Range 1.8 to 8.0 V
- ON/OFF Range 1.5 to 8.0 V
- ESD Rating of 3000 V
- Pb−Free Package is Available

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating			Symbol	Value	Unit
Input Voltage (V_{DSS}, P−Ch)			V_{IN}	8.0	V
ON/OFF Voltage (V_{GS}, N−Ch)			$V_{ON/OFF}$	8.0	V
Continuous Load Current (Note 1)	Steady State	T_A = 25°C	I_L	±1.3	A
		T_A = 85°C		±0.9	
Power Dissipation (Note 1)	Steady State	T_A = 25°C	P_D	0.40	W
		T_A = 85°C		0.20	
Pulsed Load Current	t_p = 10 μs		I_{LM}	±3.9	A
Operating Junction and Storage Temperature			T_J, T_{STG}	−55 to 150	°C
Source Current (Body Diode)			I_S	−0.4	A
ESD Rating, MIL−STD−883D HBM (100 pF, 1.5 kΩ)			ESD	3.0	kV
Lead Temperature for Soldering Purposes (1/8″ from case for 10 s)			T_L	260	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Junction−to−Ambient − Steady State (Note 1)	$R_{\theta JA}$	320	°C/W
Junction−to−Foot − Steady State (Note 1)	$R_{\theta JF}$	220	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface−mounted on FR4 board using 1 inch sq pad size (Cu area = 1.127 in sq [1 oz] including traces).

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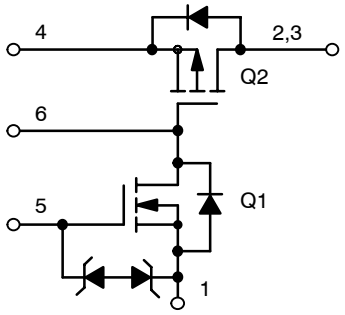
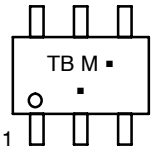
$V_{(BR)DSS}$	$R_{DS(on)}$ TYP	I_D MAX
8.0 V	130 mΩ @ −4.5 V	±1.3 A
	170 mΩ @ −2.5 V	
	260 mΩ @ −1.8 V	

SIMPLIFIED SCHEMATIC



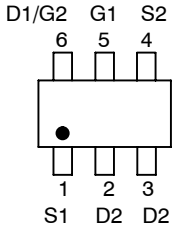
SC−88
(SOT−363)
CASE 419B
STYLE 30

MARKING DIAGRAM



TB = Device Code
M = Date Code
▪ = Pb−Free Package
(Note: Microdot may be in either location)

PIN ASSIGNMENT



ORDERING INFORMATION

Device	Package	Shipping†
NTJD1155LT1	SC−88	3000/Tape & Reel
NTJD1155LT1G	SC−88 (Pb−Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Q2 Drain−to−Source Breakdown Voltage	V_{IN}	V_{GS2} = 0 V, I_{D2} = 250 μA		−8.0			V
Forward Leakage Current	I_{FL}	V_{GS1} = 0 V, V_{DS2} = −8.0 V	T_J = 25°C			1.0	μA
			T_J = 125°C			10	
Q1 Gate−to−Source Leakage Current	I_{GSS}	V_{DS1} = 0 V, V_{GS1} = ±8.0 V				±100	nA
Q1 Diode Forward On−Voltage	V_{SD}	I_S = −0.4 A, V_{GS1} = 0 V			−0.8	−1.1	V
ON CHARACTERISTICS							
ON/OFF Voltage	$V_{ON/OFF}$			1.5		8.0	V
Q1 Gate Threshold Voltage	$V_{GS1(th)}$	V_{GS1} = V_{DS1}, I_D = 250 μA		0.4		1.0	V
Input Voltage	V_{IN}	V_{GS1} = V_{DS1}, I_D = 250 μA		1.8		8.0	V
Q2 Drain−to−Source On Resistance	$R_{DS(on)}$	$V_{ON/OFF}$ = 1.5 V	V_{IN} = 4.5 V, I_L = 1.2 A		130	175	mΩ
			V_{IN} = 2.5 V, I_L = 1.0 A		170	220	
			V_{IN} = 1.8 V, I_L = 0.7 A		260	320	
Load Current	I_L	V_{DROP} ≤ 0.2 V, V_{IN} = 5.0 V, $V_{ON/OFF}$ = 1.5 V		1.0			A
		V_{DROP} ≤ 0.3 V, V_{IN} = 2.5 V, $V_{ON/OFF}$ = 1.5 V		1.0			

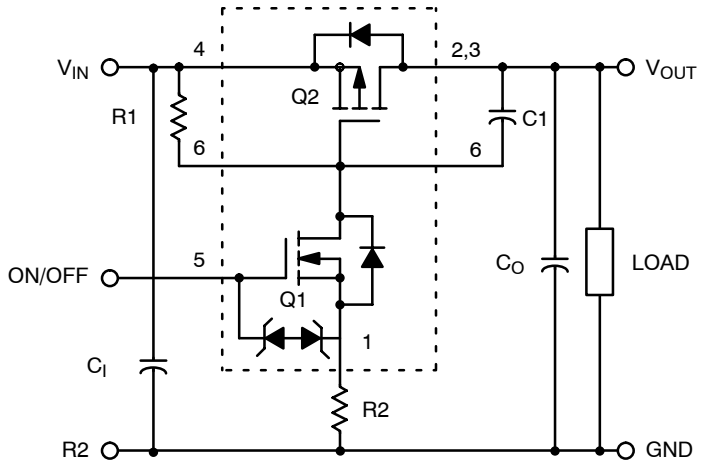


Figure 1. Load Switch Application

Components	Description	Values
R1	Pullup Resistor	Typical 10 kΩ to 1.0 MΩ*
R2	Optional Slew−Rate Control	Typical 0 to 100 kΩ*
C_O, C_I	Output Capacitance	Usually < 1.0 μF
C1	Optional In−Rush Current Control	Typical ≤ 1000 pF

*Minimum R1 value should be at least 10 x R2 to ensure Q1 turn−on.

TYPICAL PERFORMANCE CURVES (T_J = 25°C unless otherwise noted)

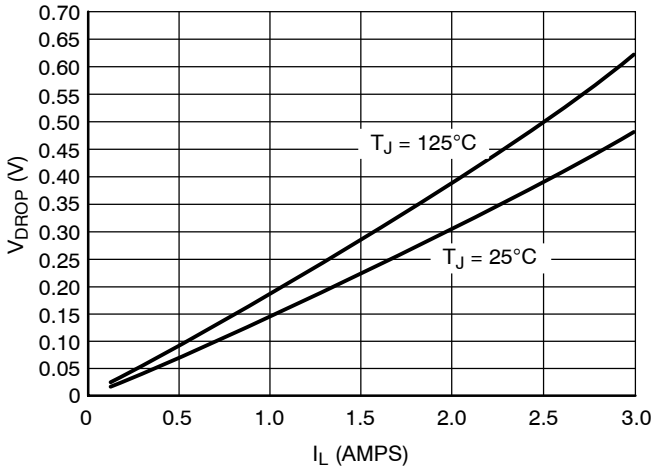


Figure 2. V_{drop} vs. I_L @ V_{in} = 2.5 V

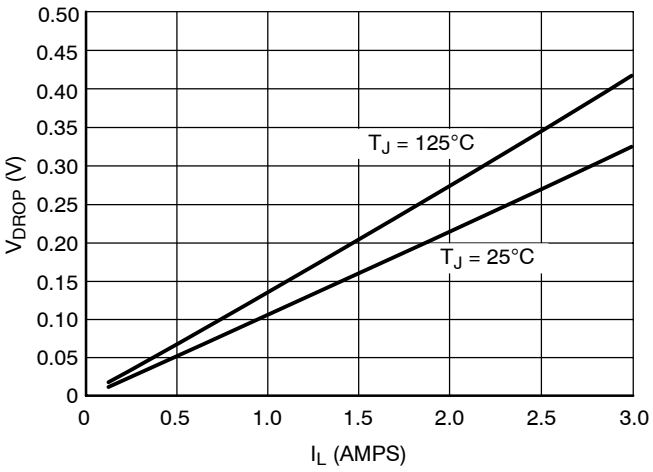


Figure 3. V_{drop} vs. I_L @ V_{in} = 4.5 V

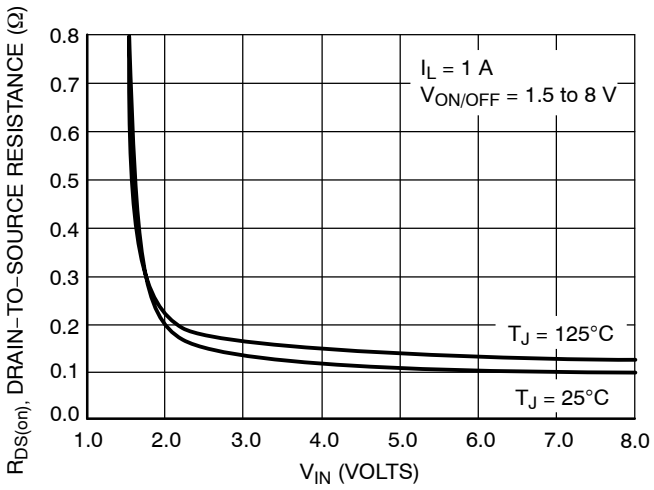


Figure 4. On−Resistance vs. Input Voltage

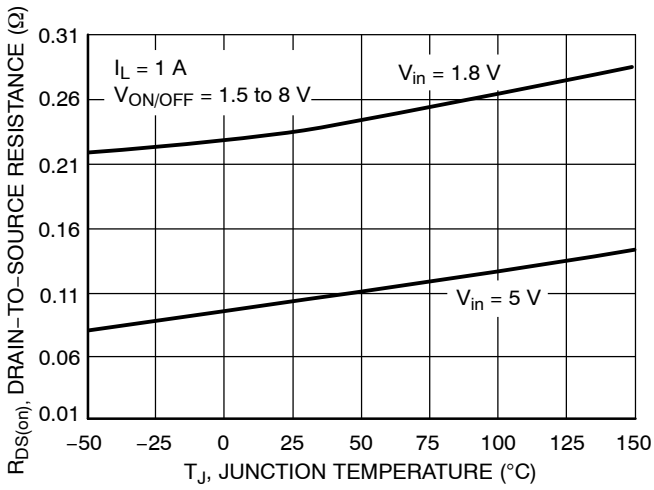


Figure 5. On−Resistance Variation with Temperature

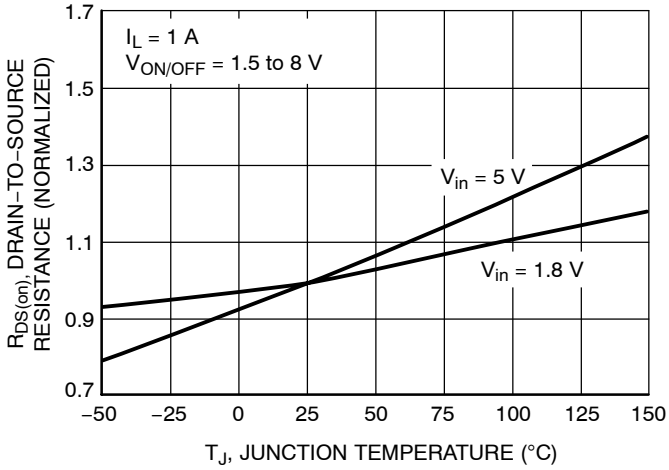


Figure 6. Normalized On−Resistance Variation with Temperature

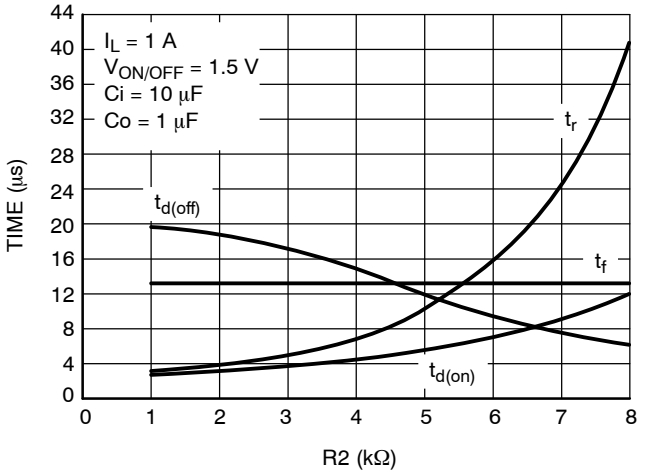


Figure 7. Switching Variation R2 @ V_{in} = 4.5 V, R1 = 20 kΩ

TYPICAL PERFORMANCE CURVES (T_J = 25°C unless otherwise noted)

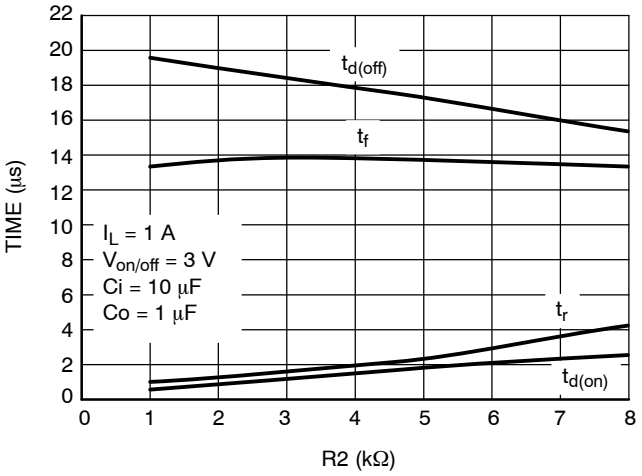


Figure 8. Switching Variation R2 @ V_{in} = 4.5 V, R1 = 20 kΩ

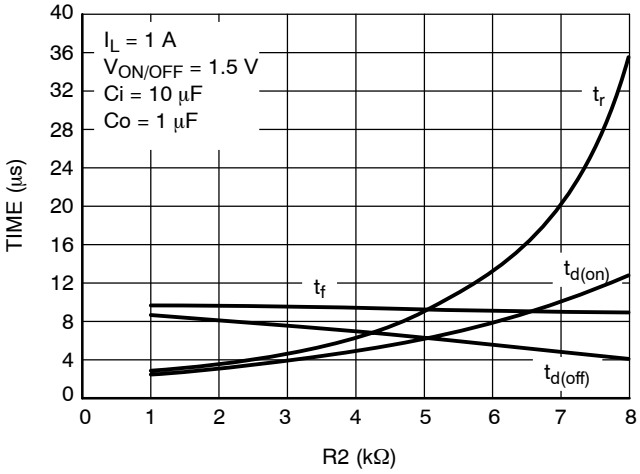


Figure 9. Switching Variation R2 @ V_{in} = 2.5 V, R1 = 20 kΩ

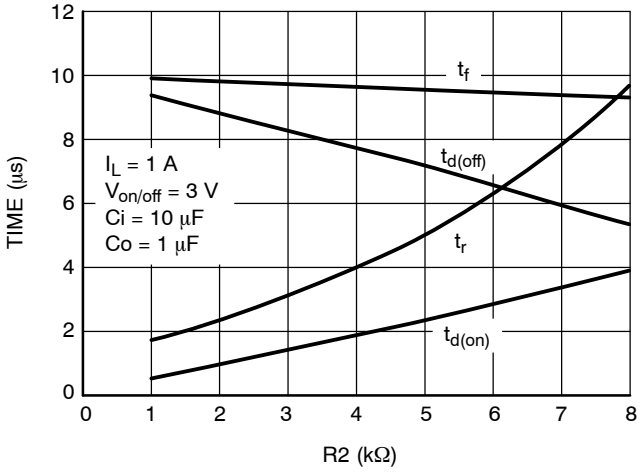


Figure 10. Switching Variation R2 @ V_{in} = 2.5 V, R1 = 20 kΩ

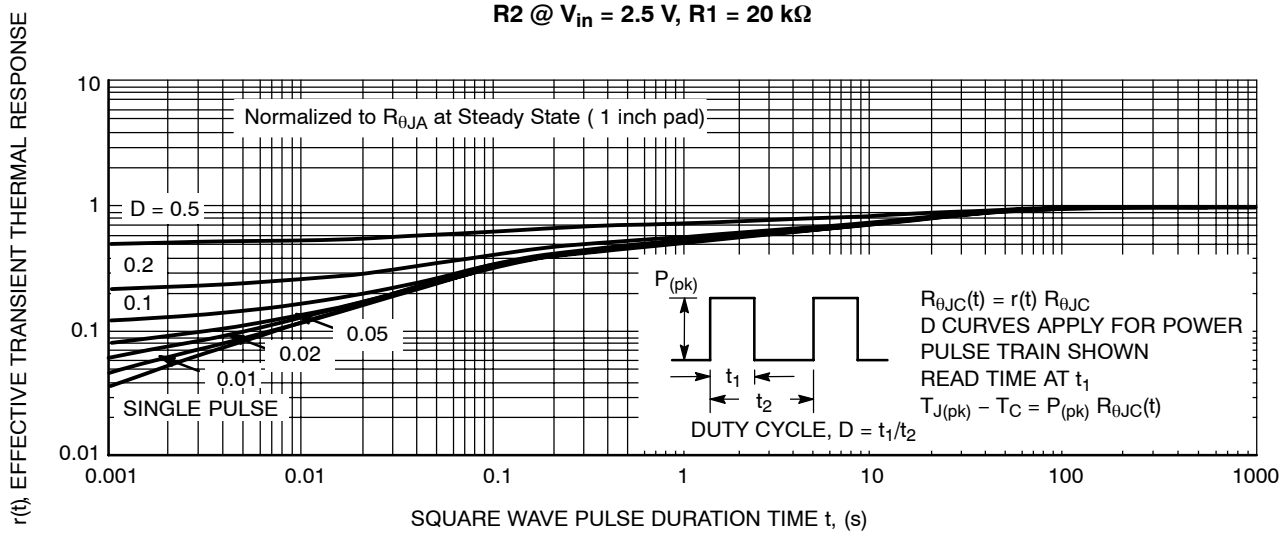
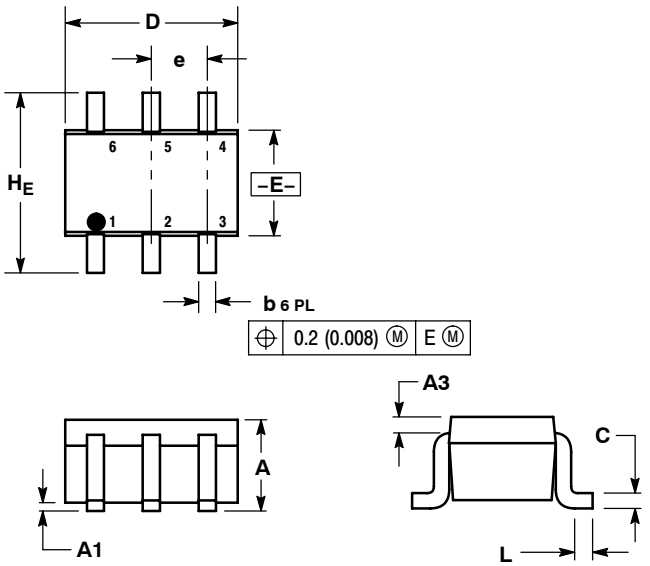


Figure 11. FET Thermal Response

PACKAGE DIMENSIONS

SC−88 (SOT−363)
CASE 419B−02
ISSUE W

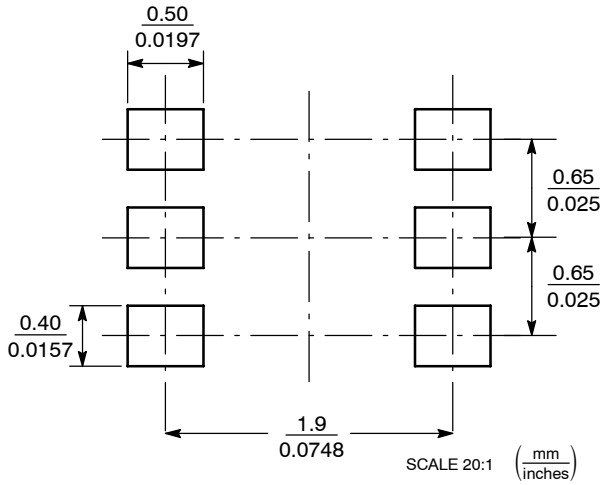


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 419B−01 OBSOLETE, NEW STANDARD 419B−02.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.95	1.10	0.031	0.037	0.043
A1	0.00	0.05	0.10	0.000	0.002	0.004
A3		0.20 REF			0.008 REF	
b	0.10	0.21	0.30	0.004	0.008	0.012
C	0.10	0.14	0.25	0.004	0.005	0.010
D	1.80	2.00	2.20	0.070	0.078	0.086
E	1.15	1.25	1.35	0.045	0.049	0.053
e		0.65 BSC			0.026 BSC	
L	0.10	0.20	0.30	0.004	0.008	0.012
H_E	2.00	2.10	2.20	0.078	0.082	0.086

STYLE 30:
PIN 1. SOURCE 1
2. DRAIN 2
3. DRAIN 2
4. SOURCE 2
5. GATE 1
6. DRAIN 1

SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
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